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View Online at https://aerobasegroup.com/nsn/5961-01-276-2464

Inclosure Material:

Metal

Overall Length:

0.260 inches

Terminal Length:

0.750 inches

Overall Diameter:

0.370 inches

Function For Which Designed:

Rectifier

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Terminal

Terminal Circle Diameter:

0.1414 inches

Features Provided:

Hermetically sealed case and quality assurance level tx

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

1.0 gate trigger voltage, dc and 50.0 reverse voltage, peak

Current Rating Per Characteristic:

350.00 microamperes forward current, total rms preset

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnpn

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

3 uninsulated wire lead

Specification Data:

81349-mil-s-19500/276 government specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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